

ABSTRACT OF THE DISCLOSURE

A method that can readily form a cavity structure between metallic wirings in, for example, semiconductors using a polyamic acid and/or a polyimide obtained by reacting a specific alicyclic tetracarboxylic acid dianhydride and a specific alicyclic diamine. The method includes a step of coating the surface of a first dielectric film formed on a semiconductor substrate with a polyamic acid and/or a polyimide, a step of patterning a cavity-forming polymer between the multilayered wirings, a step of forming a second dielectric film on the cavity-forming polymer between the multilayered wirings containing a metallic wiring, and a step of removing the cavity-forming polymer between the multilayered wirings by heating to form a cavity between the metallic wirings.